

Application Serial No. 10/826,034
Reply to Office Action of July 26, 2005

PATENT
Docket: CU-3692

Amendments To The Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1. (Currently amended) A method for manufacturing a semiconductor package, the method comprising the steps of:

attaching a bottom surface of a semiconductor wafer to a first supporting member;

thin-filming the semiconductor wafer after the step of attaching the bottom surface of the semiconductor wafer to the first supporting member;

forming a through hole in the semiconductor wafer after the step of thin-filming the semiconductor wafer;

separating the semiconductor wafer from the first supporting member;

forming an insulating layer on at least the bottom surface of the semiconductor wafer and the inner wall of the through hole;

forming a conducting layer underneath the semiconductor wafer, the conducting layer spanning at least the bottom of the through hole; and

forming a conductive member in the through hole and in electrical contact with the conducting layer;

wherein the conducting layer is formed by using at least one of a metal plate and metal foil as a material for the conducting layer;

wherein the conductive member is formed by plating;

wherein the conductive member is formed in the through hole in a manner filling

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the through hole.

2. (cancelled)
3. (cancelled)
4. (original) The method as claimed in claim 1, further comprising a step of removing at least a portion of the conducting layer.
5. (original) The method as claimed in claim 4, wherein a portion of the conducting layer beneath the conducting member is left remaining in the step of removing at least a portion of the conducting layer.
6. (original) The method as claimed in claim 1m wherein the conducting layer is a tape member.
7. (original) The method as claimed in claim 1, wherein the through hole is formed by etching.
8. (original) The method as claimed in claim 1, wherein the insulating layer is formed on the surface of the semiconductor wafer by forming an inorganic insulating layer on the surface of the semiconductor wafer, and forming an organic insulating layer on the surface of the inorganic insulating layer.
9. (original) The method as claimed in claim , wherein a barrier layer is formed on the insulating layer subsequent to the step of forming the insulating layer.
10. (currently amended) A method for manufacturing a semiconductor package, the method comprising the steps of:

attaching a bottom surface of a semiconductor wafer to a first supporting member;

thin-filming the semiconductor wafer after the step of attaching the bottom

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surface of the semiconductor wafer to the first supporting member;

forming a through hole in the semiconductor wafer after the step of thin-filming
the semiconductor wafer;

separating the semiconductor wafer from the first supporting member;

forming an insulating layer on at least the bottom surface of the semiconductor
wafer and the inner wall of the through hole;

attaching the semiconductor wafer to a top surface of a second supporting
member, the top surface spanning at least the bottom of the through hole;

forming a conducting layer on at least the bottom of the through hole; and

forming a conductive member in the through hole;

wherein the conductive member is formed by plating;

wherein the conductive member is formed in the through hole in a manner filling
the through hole.

11. (cancelled)

12. (cancelled)

13. (original) The method as claimed in claim 10, wherein the through hole is formed
by etching.

14. (original) The method as claimed in claim 10, wherein the insulating layer is
formed on the surface of the semiconductor wafer by forming an inorganic insulating
layer on the surface of the semiconductor wafer, and forming an organic insulating layer
on the surface of the inorganic insulating layer.

15. (original) The method as claimed in claim 10, wherein a barrier layer is formed on
the insulating layer subsequent to the step of forming the insulating layer.